



#### **30V P-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C		
-30V	10mΩ @ V <sub>GS</sub> = -10V	-11.5A		
	18mΩ @ V <sub>GS</sub> = -4.5V	-8.7A		

## Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## Applications

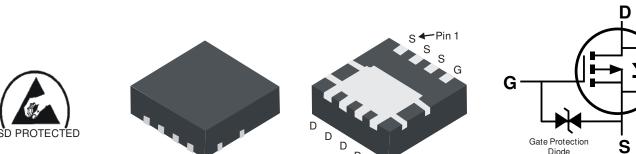
- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

### **Features and Benefits**

- Low R<sub>DS(ON)</sub> Ensures On-State Losses Are Minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **ESD** Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

## **Mechanical Data**

- Case: POWERDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)



POWERDI3333-8

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3017SFGQ-7	POWERDI3333-8	2,000/Tape & Reel
DMP3017SFGQ-13	POWERDI3333-8	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

Top View

2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

D

**Bottom View** 

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

POWERDI is a registered trademark of Diodes Incorporated.

Equivalent Circuit



## **Marking Information**



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P17= Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year (ex: 13 = 2013) WW = Week code  $(01 \sim 53)$ 

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Noto 7) // 10//	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-11.5 -9.4	А
Continuous Drain Current (Note 7) $V_{GS} = -10V$	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-15.2 -12.1	А
Maximum Continuous Body Diode Forward Current (Note 6)			Is	-3.0	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	-80	А
Avalanche Current (Note 8) L = 1mH			I <sub>AR</sub>	14	А
Repetitive Avalanche Energy (Note 8) L = 1mH			E <sub>AR</sub>	104	mJ

### **Thermal Characteristics**

Notes:

Characteristic	Symbol	Value	Units		
Total Bower Dissinction (Note 6)	$T_A = +25^{\circ}C$	D	0.94	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	0.6	vv	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	137	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	82	°C/W	
Total Dower Dissinction (Nate 7)	$T_A = +25^{\circ}C$	D	2.2	W	
Total Power Dissipation (Note 7)	$T_A = +70^{\circ}C$	PD	1.3	vv	
Thermal Registeres, Junction to Ambient (Note 7)	Steady State	D	60	°C/W	
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{\theta JA}$	36	°C/W	
Thermal Resistance, Junction to Case (Note 7)		R <sub>0JC</sub>	3.0	°C/W	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout, please see http://www.diodes.com/datasheets/ap02001.pdf for latest version.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

8. I<sub>AR</sub> and E<sub>AR</sub> rating are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ 



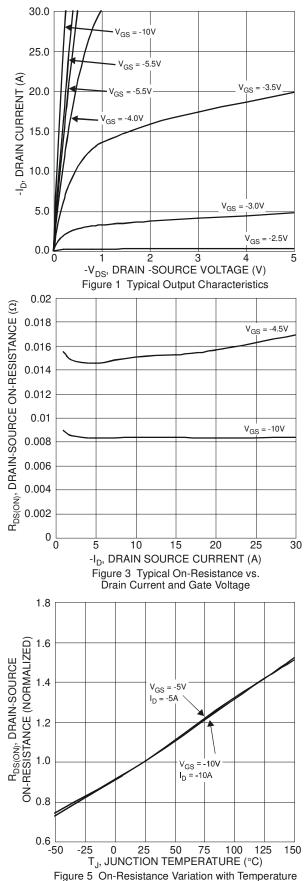
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

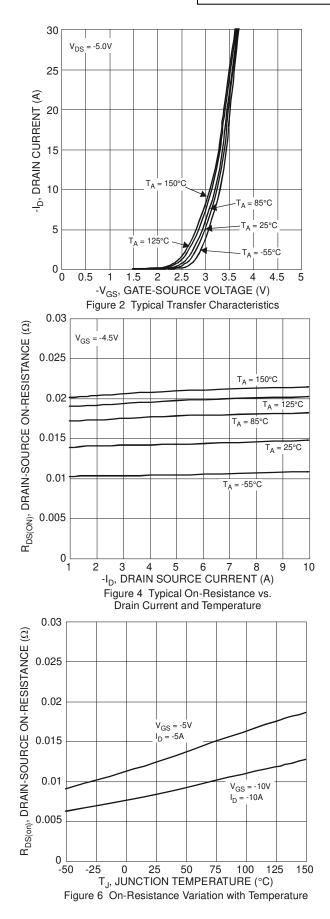
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30			V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μA	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_		±10	μA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	<u> </u>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	_	-3.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	P	_	8.5	10	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -11.5A	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	15	18		$V_{GS} = -4.5V, I_D = -8.5A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	24		S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -11.5A	
DYNAMIC CHARACTERISTICS (Note 10)			•	•	•	•	
Input Capacitance	Ciss	_	2246	_	pF		
Output Capacitance	Coss	_	352	_	pF	<sup>−</sup> V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, − f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	294		pF		
Gate resistance	Rg	_	5.1	12	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 5V)	Qg	_	20.5	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	41		nC		
Gate-Source Charge	Q <sub>gs</sub>	_	7.6		nC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -11.5A	
Gate-Drain Charge	Q <sub>gd</sub>	_	8.0		nC		
Turn-On Delay Time	t <sub>D(on)</sub>		7.5		nS		
Turn-On Rise Time	tr	_	15.4		nS	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V,	
Turn-Off Delay Time	t <sub>D(off)</sub>		45.6		nS	$R_{G} = 6\Omega, I_{D} = -11.5A$	
Turn-Off Fall Time	t <sub>f</sub>	_	36.8	—	nS		
BODY DIODE CHARACTERISTICS	•				•	1	
Diode Forward Voltage	V <sub>SD</sub>	_	-0.7		V	$V_{GS} = 0V, I_{S} = -1A$	
Reverse Recovery Time (Note 9)	t <sub>rr</sub>	_	20		nS		
Reverse Recovery Charge (Note 9)	Q <sub>rr</sub>	_	9.5	_	nC	- I <sub>S</sub> = -11.5A, dl/dt = 100A/μs	

9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing. Notes:

## DMP3017SFGQ

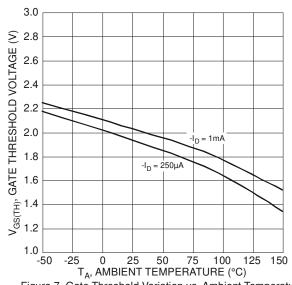


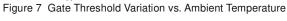


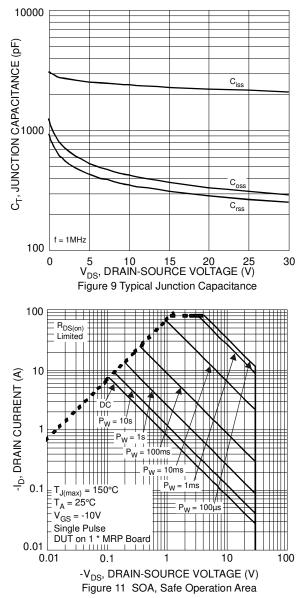


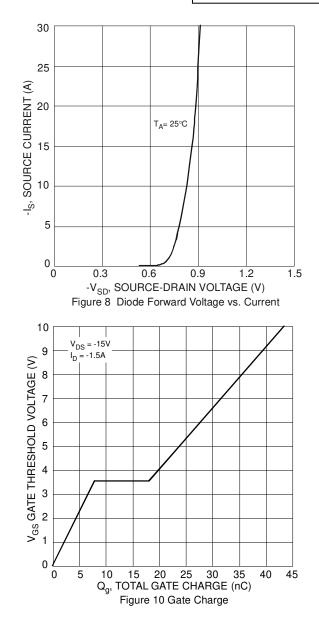
## DMP3017SFGQ



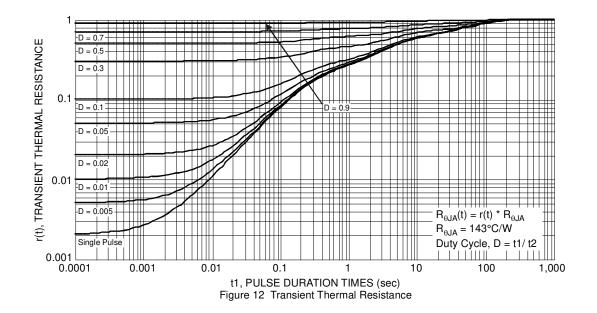








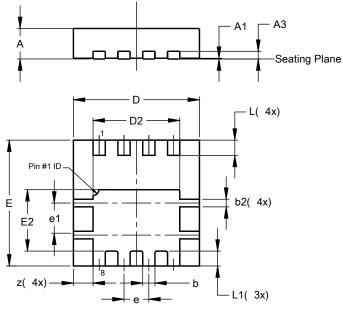






## Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

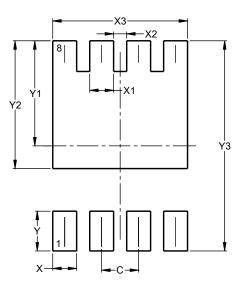


POWERDI <sup>®</sup> 3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	_	-	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
е	-	-	0.65			
e1	0.79	0.89	0.84			
L	0.35	0.45	0.40			
L1	_	_	0.39			
z	_	_	0.515			
	All Dimensions in mm					

#### POWERDI3333-8

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



#### POWERDI3333-8

Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
X3	2.370		
Y	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		



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